

Page 12, line 11, after "distance" insert --therebetween--;  
line 18, after "portions" insert --of film 12--;  
line 27, change "to have a pattern" to --into distinct regions--;  
line 28, change "is" to --are-- and then add --of these regions-- at the  
end of the line; and  
line 29, after "10a" insert --(Fig.3D)--.

**IN THE CLAIMS:**

Kindly amend claim 1 as follows:

*Su*  
*B*  
*G*  
1. ~~(Amended)~~ A method for manufacturing a semiconductor device having a buried conductive layer which is connected to one of a source and a drain of a MOS transistor and extends over a gate electrode of said MOS transistor, said method comprising the steps of:

forming a first insulating film on a semiconductor substrate;

forming a first conductive film as said gate electrode and a second insulating film on said first insulating film, said gate electrode having a width equal to a minimum processing size achievable with a lithographic process technique;

forming a third insulating film on the whole surface of said semiconductor substrate having said first insulating film, said first conductive film and said second insulating film formed thereon;